# APR 0 1 2004 E

#### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of: Wai M. LEE et al.

Confirmation No.: 5303

Application No.: 10/694,999

Art Unit: 1756

Filed: October 29, 2003

Examiner: To Be Assigned

For: APPARATUS FOR SUBSTRATE

PRE-TREATMENT

Attorney Docket No.: 060937-0226-US

### TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above-identified application.

Please change the attorney docket number to 060937-0226-US. Future correspondence should be forwarded to Christopher G. Hayden, Customer No. **009629**.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310.

Respectfully submitted,

Christopher G. Hayden

Date April 1, 2004

44,750

Customer Number 009629

Morgan, Lewis & Bockius LLP 1111 Pennsylvania Avenue, N.W. Washington, D.C. 20004 202-739-3001 (facsimile)



#### REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P. O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, Customer Number 009629, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer No. 009629, Patent Support Unit, Morgan, Lewis & Bockius LLP, 1111 Pennsylvania Avenue, N.W., Washington, D.C. 20004, and direct all telephone calls to Morgan, Lewis & Bockius LLP at 202-739-3000.

Assignee:

EKC Technology, Inc.

Date: 29 March 2004

Signature:

Typed Name Michael A. Fury

Position/Title Vice President, R&D and Engineering

Address:

2520 Barrington Court, Hayward, California 94545

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Schedule A						
App.#L./	JHe .	Jinventor(s)	Filing - Date	New Attorney = Docket No.	Former Attorney Docket No.	
	Compositions for Cleaning Organic					
20,000,004	and Plasma Etched Residues for		07400004			
09/903,064	Semiconductor Devices  Method of and Apparatus for	Small, et al.	07/10/2001	60937-091-US	8317-091-999	
09/874,330	Substrate Pre-Treatment	Molonov et al	06/06/2001	60027 444 110	0247 444 000	
09/6/4,330	Chemical Mechanical Polishing	Maloney, et al.	00/00/2001	60937-111-US	8317-111-999	
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999	
00.000,0.0	Oxalic Acid as a Semiaqueous		· // 00/2001	00001 111 00	0011 114 000	
	Cleaning Product for Copper and			·	ļ	
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999	
	Sulfoxide Pyrolid(in)one Alkanolamine					
10/193,185	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999	
			;			
00/070 044	Method for the Deposition of Materials		00/00/0004	00007.400.110	0047 400 000	
09/876,944	from Mesomorphous Films  Post Etch Cleaning Composition for	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999	
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999	
10/00/,104	Photolytic Conversion Process to	r ayrie, et al.	12/04/2001	00937-123-03	0317-123-999	
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999	
	Cleaning Solutions Including	, , , , , , , , , , , , , , , , , , , ,				
	Nucleophilic Amine Compound					
1	Having Reduction and Oxidation					
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999	
	Method and Compositions for					
40/000 400	Chemically Treating A Substrate	<b>.</b>	0.4/0.0/0.00			
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999	
	Cleaning Solution Including Nucleophilic Amine Compound					
	Having Reduction and Oxidation					
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999	
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-137-999	
	Process for the Use of Bis-Choline		<u></u>			
	and Tris-Choline in the Cleaning of					
	Quartz-Coated Polysilicon and Other				·	
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999	
	Cleaning Compositions Containing					
	Hydroxylamine Derivatives and					
10/000 000	Process Using Same for Residue					
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999	
	Composition for Exfeliation Asset to					
10/689,616	Composition for Exfoliation Agent to be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317 141 000	
10,000,010	Reducing Oxide Loss When Using	Wiciviii N. Caltel	10/22/2003	00337-141-03	8317-141-999	
i	Fluoride Chemistries to Remove Post-		•	{ 1		
	Etch Residues in Semiconductor		,			
60/467,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888	

			Filing	New Attorney	Former Attorney
	Title 7	i.⊱⊮ Inventor(s) ⁄∷i.	Date I	Docket No.	
	Method for Depositing Patterned				
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver				
40746 020	and Silver Oxide Films and Patterned	D	44400000		
10/716,838	Films Semiconductor Process Residue	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
10/162,679	Removal Composition and Process	Lee et al	06/06/2002	60027 440 UC	9247 440 000
10/102,079	System and Method for Cleaning	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
		y, o		00007 100 1 10	0017-100-000
	Abrasive-Free Chemical Mechanical				,
	Polishing Composition and Polishing	:	·		
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
10/004 107	Method of Depositing Nanostructured				
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
10/280,270	Hydrothermal Treatment of Nanostructured Films	Mandaharina adad	40/00/0000	00007 407 110	0047 407 000
10/257,469	Inhibition of Titanium Corrosion	Mukherjee, et al.  Daviot, et al.	10/23/2002	60937-167-US	8317-167-999
10/237,409	Chemical Mechanical Polishing	Daviol, et al.	10/11/2002	60937-168-US	8317-168-999
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
107 10 1, 100	Aqueous Phosphoric Acid	Oman, or an	00/21/2003	00937-17 1-03	0317-171-999
	Compositions for Cleaning				
10/688,900	Semiconductor Devices	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical				
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
	Automated Dense Phase Fluid				
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
00/455 400	Electrohydrodynamic Cleaning of				
60/455,439	Semiconductors	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
	Free Radical-Forming Activator				
40/004 000	Attached to Solid and Used to				
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
10/277 522	Titanium Carboxylate Films for Use in	11:00 -4 -1	00/00/0000		
10/377,533	Semiconductor Processing Method of Making Barrier Layers	Hill, et al. Maloney, et al.	02/26/2003	60937-182-US	8317-182-999
10/422,000	Remover Formulation Containing	Maioriey, et al.	05/20/2003	60937-183-US	8317-183-999
	Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
	Cleaning Composition for Removing	- Industry, or all	3-11-12-003		0017-100-000
	Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
	Deposition of Permanent Polymer	· · · · · · · · · · · · · · · · · · ·			· · · · · · · · · · · · · · · · · · ·
10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

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App #	. ∓ Title i	Inventor(s)	Filing Dale	new Attorney Docket No.	Former Attorney  Docket No.
asappanism	Seimconductor Process Residue			MADOUNETANO.	a Dockerno.
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,000	Cleaning Compositions and Method of	L	00/20/2000	00007 100 00	0011-100-000
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10,000,000	Compositions and Methods for		0.7,00,2000	00001 10 1 00	0017 104 000 1
	Rapidly Removing Overfilled		·		,
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				33 200 000
	Titanium, Polysilicon, and Other				
	Substrates Using Organosulfonic	, , , , , , , , , , , , , , , , , , ,			
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
•	PeriodicAcid Compositions for				
	Polishing Nobel Metal/High K	· .			
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	·	·			
	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
	Periodic Acid Compositions for			•	
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing	_			
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
,			,		·
	Chemical Mechanical Polishing				
00/500 054	Slurries and Cleaners Containing	Tamilarani akad	00/40/0000	00007.044.00	0047.044.000
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
10/003,417	Alumina Abrasive for Chemical	Siliali, et al.	09/22/2003	00937-213-03	0317-213-999
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
00/020,107	Particulate or Particle-Bound	Onono, ot ai.	12/02/2003	30301-210-117	3317-210-000
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound				0011 211 000
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI	<u>'</u>			
	Features on Semiconductors: Water		·		-
60/533,054	Polishing with Ceria Sturries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
	Removal of Post Etch Residues and				:
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				İ
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
	Method and Apparatus for Substrate				
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888